



GaAs Schottky Diode Series Pair Tee

Technical Data

HSCH-9501

Features

- **Low Junction Capacitance**— typically 40 fF
- **Low Series Resistance**— typically 3 Ω
- **Large Bond Pads Suitable for Wire-bond or Flip-chip Assembly**
- **Polyimide Scratch Protection**

Description

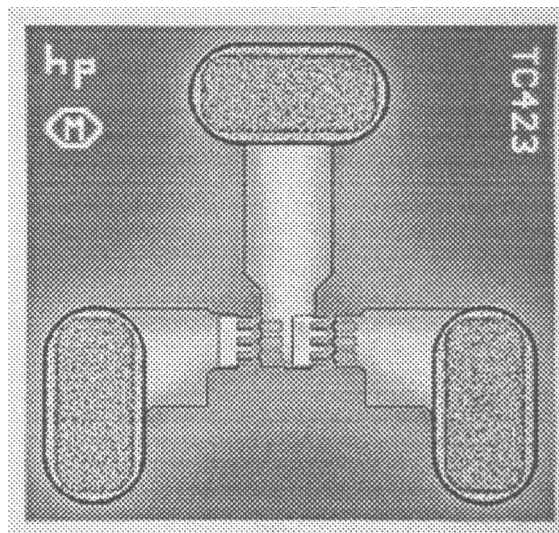
The HSCH-9501 is an integrated series pair of GaAs Schottky barrier diodes in a Tee configuration. It is a beamless version of the HSCH-9201 series pair beam lead diode.

Applications

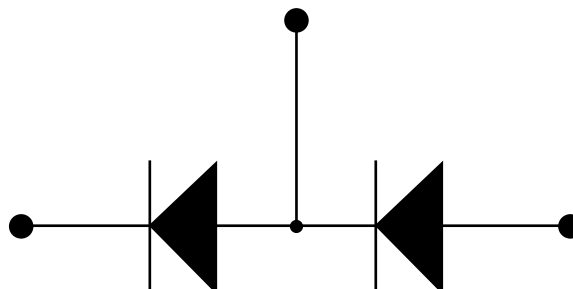
The HSCH-9501 is a high-performance millimeter wave diode that can be used as a balanced mixer or frequency multiplier in microwave and millimeter wave transceivers.

Specifications

- V_F (1 mA): 700-800 mV
- V_F (10 mA): 800-850 mV
- R_S (5 mA): <6 Ω
- B_V (-10 mA): >4.5 V
- C_J (per diode): <0.050 pF



Chip Size:	620 x 595 μm (24.4 x 23.4 mils)
Chip Size Tolerance:	$\pm 10 \mu\text{m}$ (± 0.4 mils)
Chip Thickness:	100 μm (4 mils)
Chip Thickness Tolerance:	$\pm 15 \mu\text{m}$ (± 0.6 mils)
Bond Pad Sizes:	100 x 200 μm (3.9 x 7.9 mils)





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This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local Agilent sales representative.

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Data subject to change.

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5968-4223E (11/99)